

Title (en)
METHOD OF PROCESSING A MONOCRYSTALLINE SEMICONDUCTOR DISK AND PARTIALLY PROCESSED SEMICONDUCTOR DISK

Title (de)
VERFAHREN ZUR PROZESSIERUNG EINER MONOKRISTALLINEN HALBLEITERSCHEIBE UND TEILWEISE PROZESSIERTE HALBLEITERSCHEIBE

Title (fr)
PROCEDE POUR TRAITER UNE PLAQUETTE DE SEMI-CONDUCTEUR MONOCRISTALLINE ET PLAQUETTE DE SEMI-CONDUCTEUR PARTIELLEMENT TRAITEE

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Application
EP 00929254 A 20000324

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• DE 19915078 A 19990401

Abstract (en)
[origin: DE19915078A1] The invention relates to a method for processing a monocrystalline silicon semiconductor disk (1), which method comprises an annealing step carried out at a temperature above 550 DEG C. Prior to annealing a protective layer (15) is applied to the rear side of the silicon semiconductor disk so as to prevent the penetration of metal and/or rare-earth metal substances into the silicon semiconductor disk (1) during annealing.

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H01L 21/02 (2013.01 - KR); **H01L 21/324** (2013.01 - EP US); **H01L 28/55** (2013.01 - EP US); **H10B 12/033** (2023.02 - EP US)

Citation (examination)
• US 3494809 A 19700210 - ROSS CARL A
• DD 286459 A5 19910124 - AKAD WISSENSCHAFTEN DDR [DE]
• US 5973386 A 19991026 - HORIKAWA MITSUHIRO [JP]
• PATENT ABSTRACTS OF JAPAN vol. 199, no. 712 25 November 1997 (1997-11-25)
• See also references of WO 0060646A1

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